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| First Named Inventor                                   | Leonard Forbes       |
| Serial No.   | 10/719,772           |
| Filing Date  | November 21, 2003    |
| Group Art Unit   | 2815                 |
| Examiner Name  | Unknown <i>Festy</i> |
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| Attorney Docket No.                                    | 400.252US01          |
| Title: APPARATUS AND METHOD FOR SPLIT GATE NROM MEMORY |                      |

**INFORMATION DISCLOSURE  
STATEMENT  
FORM PTO-1449**

Sheet 1 of 7

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| Examiner Name        | Unknown <i>Levy</i> |
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Title: APPARATUS AND METHOD FOR SPLIT  
GATE NROM MEMORY

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| Examiner Name   | Unknown <i>Fenay</i> |   |  |
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| Attorney Docket No.                                       | 400.252US01          |   |  |
| Title: APPARATUS AND METHOD FOR SPLIT<br>GATE NROM MEMORY |                      | Sheet 3 of 7  |  |

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| Examiner Name  | Unknown - <i>Fenty</i> |   |
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| Attorney Docket No.                                    | 400.252US01            |   |
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| Examiner Signature | <i>Amelia Fenty</i> | Date Considered | 9/2/04 |
|--------------------|---------------------|-----------------|--------|

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|--|-------------------|---|
| First Named Inventor                                   | Leonard Forbes    | <b>INFORMATION DISCLOSURE<br/>STATEMENT<br/>FORM PTO-1449</b> |
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| Group Art Unit   | 2815              |   |
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| Title: APPARATUS AND METHOD FOR SPLIT GATE NROM MEMORY |                   | Sheet 7 of 7  |

|           |   |
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|--------------------|-----------------------|-----------------|---------|
| Examiner Signature | <i>Jesse G. Fenty</i> | Date Considered | 9/24/04 |
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